

# TIP100/101/102

**SemiHow**  
Know-How for Semiconductor

# TIP100/101/102

## Monolithic Construction With Built In Base-Emitter Shunt Resistors

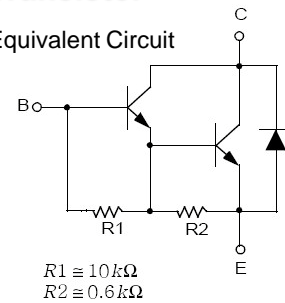
- High DC Current Gain :  $h_{FE}=1000$  @  $V_{CE}=4V$ ,  $I_C=3A$  (Min.)
- Collector-Emitter Sustaining Voltage
- Low Collector-Emitter Saturation Voltage
- Industrial Use
- Complementary to TIP105/106/107

### Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

| CHARACTERISTICS  | SYMBOL    | RATING          | UNIT             |
|--|-----------|-----------------|------------------|
| Collector-Base Voltage : TIP100<br>: TIP101<br>: TIP102    | $V_{CBO}$ | 60<br>80<br>100 | V<br>V<br>V      |
| Collector-Emitter Voltage : TIP100<br>: TIP101<br>: TIP102 | $V_{CEO}$ | 60<br>80<br>100 | V<br>V<br>V      |
| Emitter-Base Voltage                                       | $V_{EBO}$ | 5               | V                |
| Collector Current(DC)                                      | $I_C$     | 8               | A                |
| Collector Current(Pulse)                                   | $I_{CP}$  | 15              | A                |
| Base Current   | $I_B$     | 1               | A                |
| Collector Dissipation( $T_a=25^\circ\text{C}$ )            | $P_C$     | 2               | W                |
| Collector Dissipation( $T_c=25^\circ\text{C}$ )            | $P_C$     | 80              | W                |
| Junction Temperature                                       | $T_J$     | 150             | $^\circ\text{C}$ |
| Storage Temperature  | $T_{STG}$ | -65~150         | $^\circ\text{C}$ |

## NPN Epitaxial Silicon Darlington Transistor

Equivalent Circuit



TO-220

1. Base
2. Collector
3. Emitter



### Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

| CHARACTERISTICS   | SYMBOL         | Test Condition   | Min             | Max            | Unit  |
|---|----------------|--|-----------------|----------------|---|
| Collector-Emitter Sustaining Voltage : TIP100<br>: TIP101<br>: TIP102 | $V_{CEO(SUS)}$ | $I_C=30\text{mA}$ , $I_B=0$  | 60<br>80<br>100 |                | V<br>V<br>V                                     |
| Collector Cut-off Current : TIP100<br>: TIP101<br>: TIP102            | $I_{CEO}$      | $V_{CE}=30V, I_B=0$<br>$V_{CE}=40V, I_B=0$<br>$V_{CE}=50V, I_B=0$  |                 | 50<br>50<br>50 | $\mu\text{A}$<br>$\mu\text{A}$<br>$\mu\text{A}$ |
| Collector Cut-off Current : TIP100<br>: TIP101<br>: TIP102            | $I_{CBO}$      | $V_{CE}=60V, I_E=0$<br>$V_{CE}=80V, I_E=0$<br>$V_{CE}=100V, I_E=0$ |                 | 50<br>50<br>50 | $\mu\text{A}$<br>$\mu\text{A}$<br>$\mu\text{A}$ |
| Emitter Cut-off Current   | $I_{EBO}$      | $V_{EB}=5V, I_C=0$   |                 | 2              | mA  |
| DC Current Gain   | $h_{FE}$       | $V_{CE}=4V, I_C=3A$<br>$V_{CE}=4V, I_C=8A$                         | 1000<br>200     | 20000          |   |
| Collector-Emitter Saturation Voltage                                  | $V_{CE(sat)}$  | $I_C=3A, I_B=6\text{mA}$<br>$I_C=8A, I_B=80\text{mA}$              |                 | 2<br>2.5       | V<br>V  |
| Base-Emitter ON Voltage   | $V_{BE(on)}$   | $V_{CE}=4V, I_C=8A$  |                 | 2.8            | V   |
| Output Capacitance  | $C_{ob}$       | $V_{CB}=10V, I_E=0$ , $f=0.1\text{MHz}$                            |                 | 200            | pF  |

\* Pulse Test:  $PW \leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

# Typical Characteristics

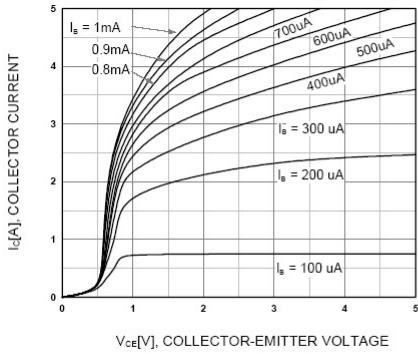


Figure 1. Static Characteristic

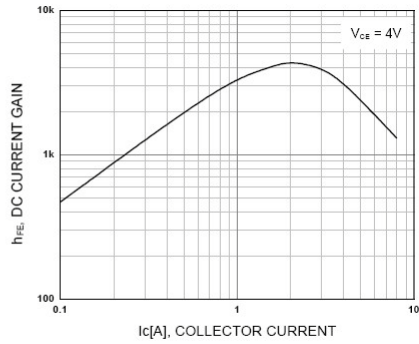


Figure 2. DC current Gain

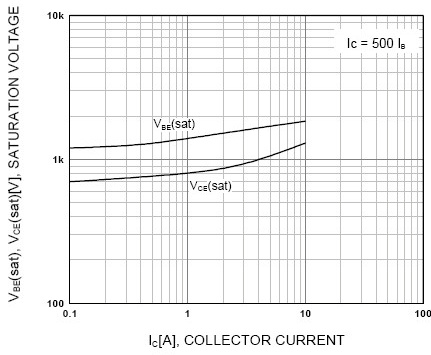


Figure 3. Collector-Emitter Saturation Voltage  
Base-Emitter Saturation Voltage

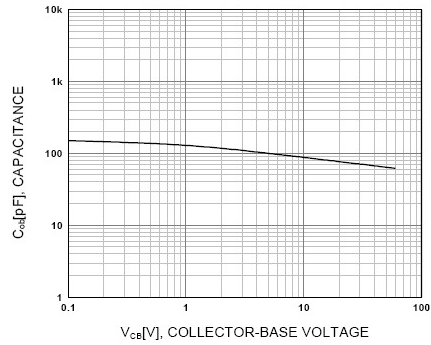


Figure 4. Collector Output Capacitance

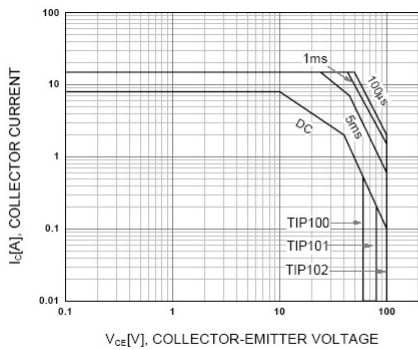


Figure 5. Safe Operating Area

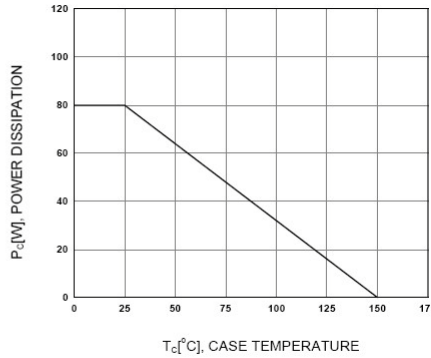
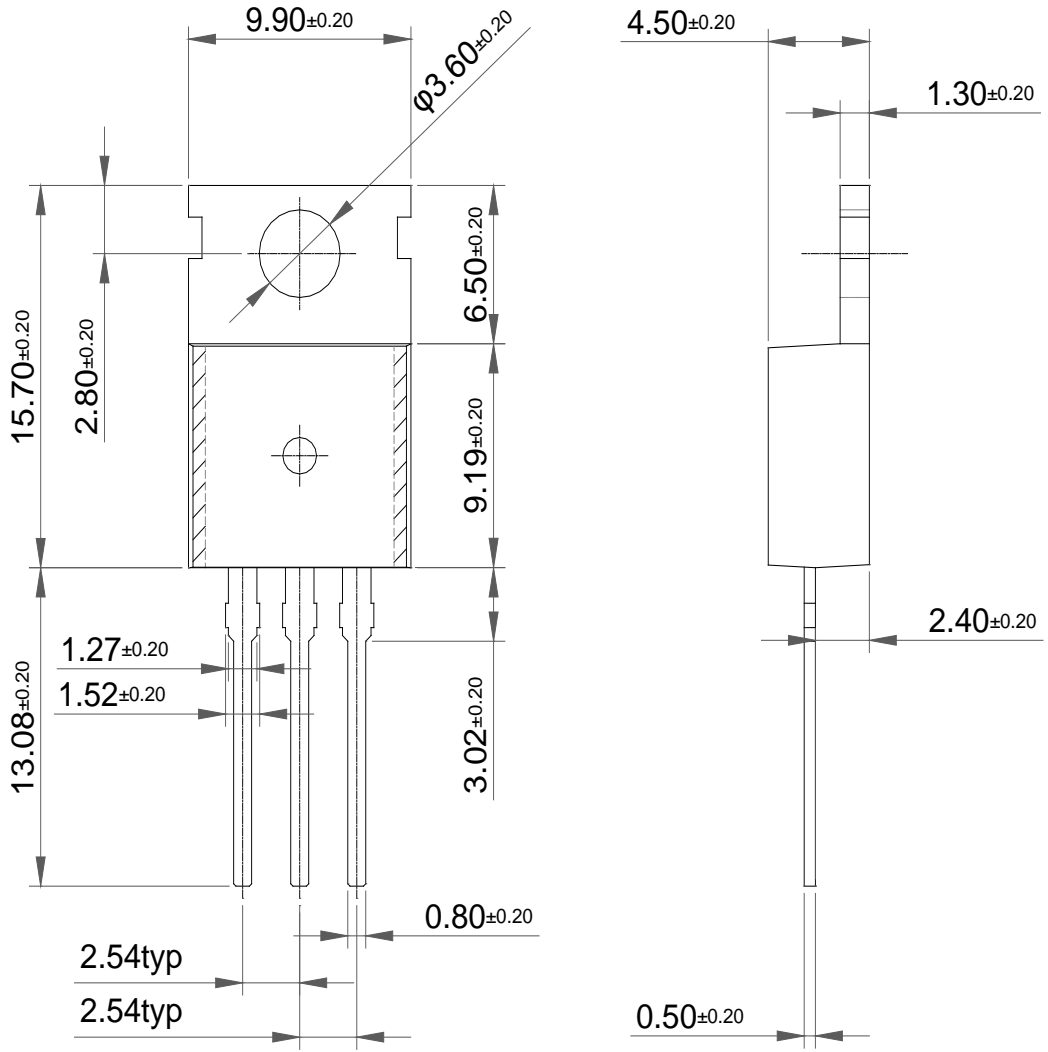


Figure 6. Power Derating

Package Dimension

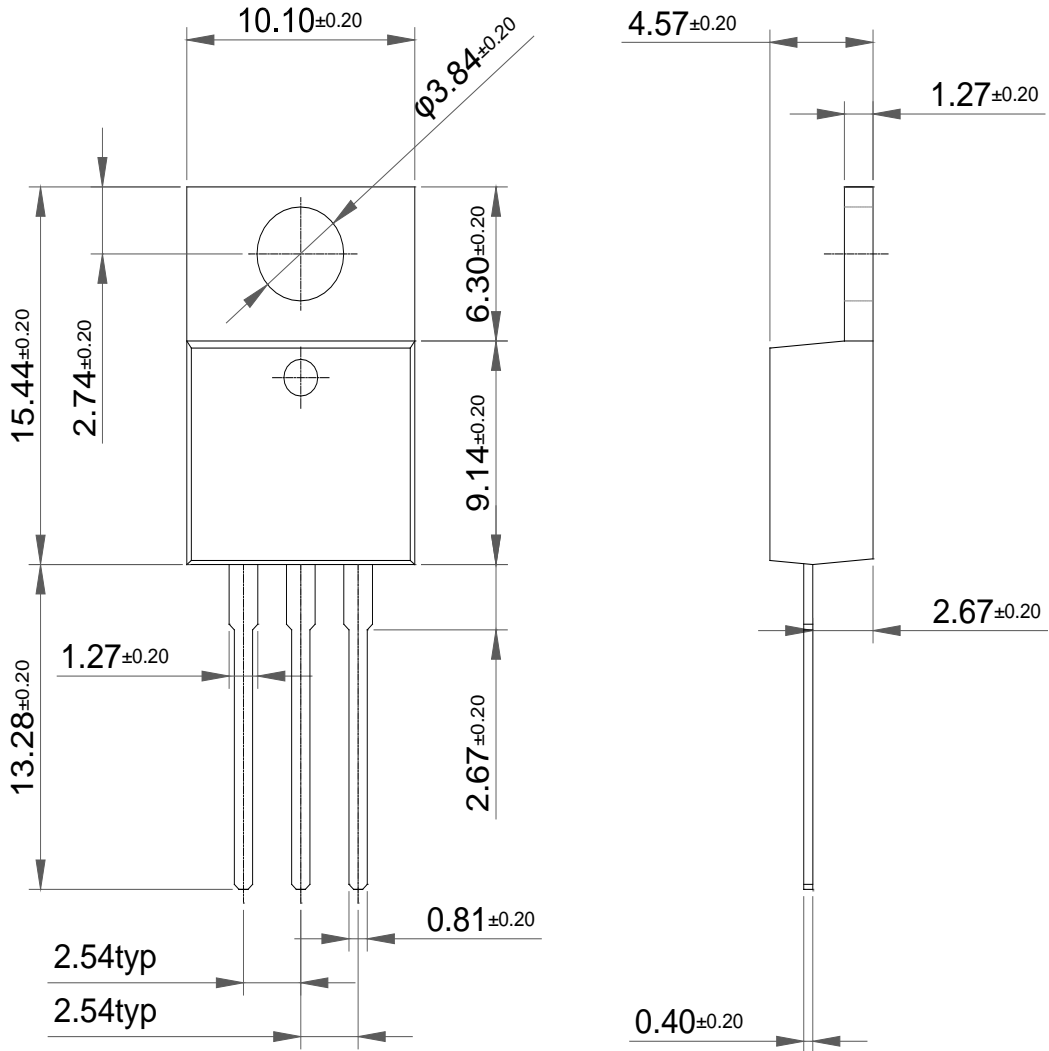
# TO-220 (A)



Dimensions in Millimeters

Package Dimension

TO-220 (B)



Dimensions in Millimeters